

## ABSTRACT OF THE DISCLOSURE

The present invention improves the quality of the TFT structure by avoiding photo-induced current, and lowers manufacturing costs by decreasing the number of masks required in the process, wherein the former 5 is achieved by the stacked structure including a gate layer, an insulation layer, an amorphous silicon layer and an ohmic contact layer, and the latter is achieved by using the stacked structure as a mask and by exposing the substrate from the back surface.

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